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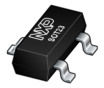


PBHV9115TLH

150 V, 1 A PNP high-voltage low VCEsat BISS transistor

16 January 2017 **Product data sheet**

1. General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8115TLH

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Small SMD plastic package
- AEC-Q101 qualified

3. Applications

- Power management
- LCD backlighting
- LED driver for LED chain module
- Switch Mode Power Supply (SMPS)

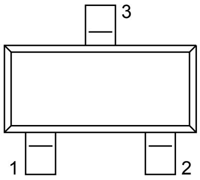
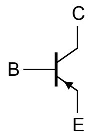
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-150	V
I_C	collector current			-	-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq$ 1 ms		-	-	-2	A
h_{FE}	DC current gain	V_{CE} = -10 V; I_C = -50 mA; T_{amb} = 25 °C		70	-	300	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 TO-236AB (SOT23)	 sym132
2	E	emitter		
3	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV9115TLH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV9115TLH	FC%

[1] % = placeholder for manufacturing site code

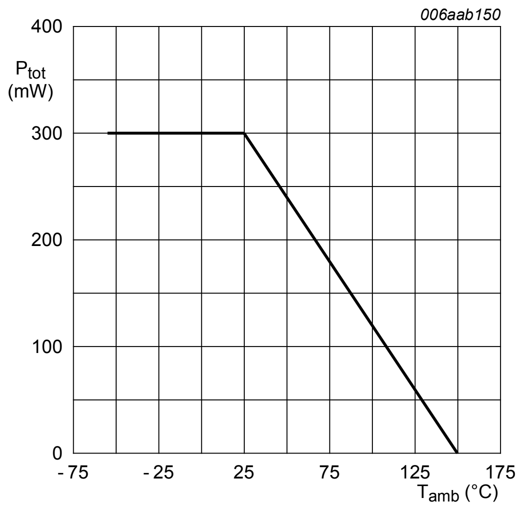
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-200	V
V_{CEO}	collector-emitter voltage	open base		-	-150	V
V_{CESM}	collector-emitter peak voltage	V_{BE} = 0 V		-	-200	V
V_{EBO}	emitter-base voltage	open collector		-	-6	V
I_C	collector current			-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq$ 1 ms		-	-2	A
I_{BM}	peak base current			-	-400	mA
P_{tot}	total power dissipation	$T_{amb} \leq$ 25 °C	[1]	-	300	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

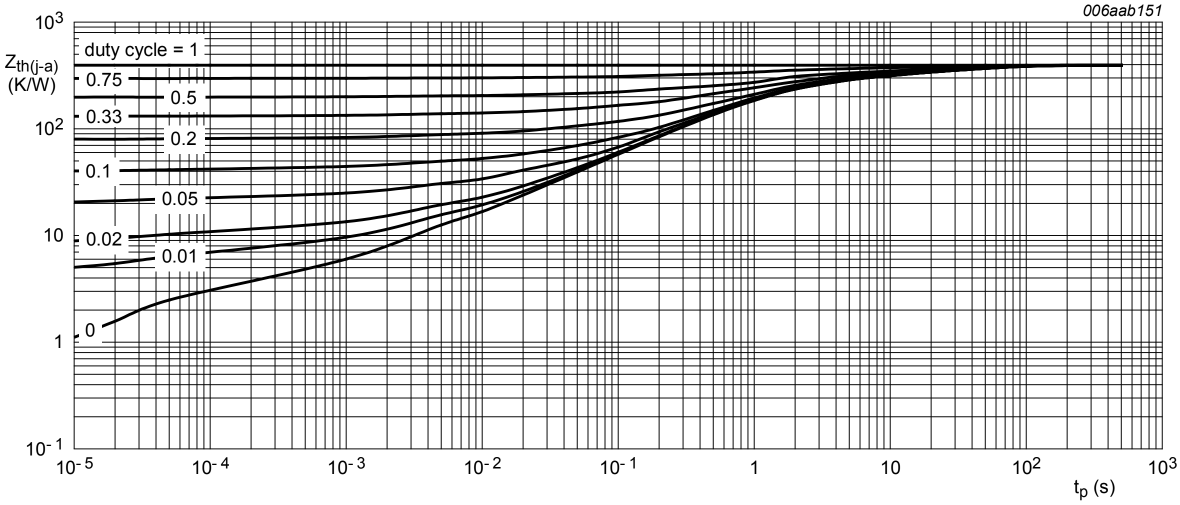
Fig. 1. Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



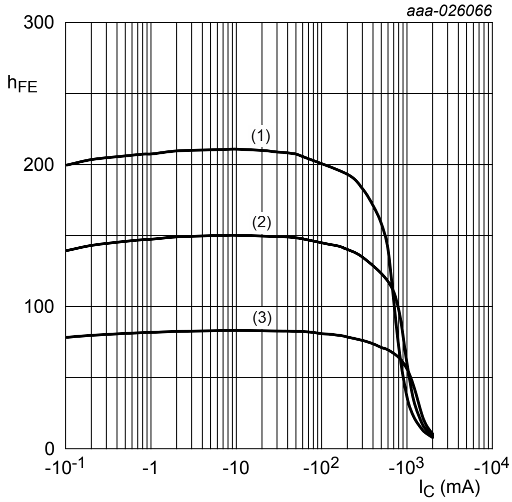
FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

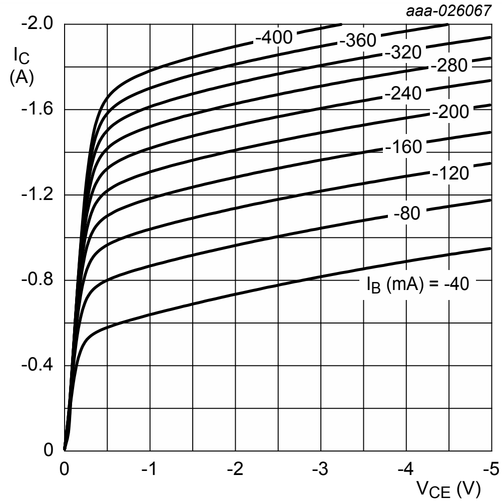
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = -120 V; I_E = 0 A; T_{amb} = 25 °C		-	-	-100	nA
		V_{CB} = -120 V; I_E = 0 A; T_j = 150 °C		-	-	-10	µA
I_{CES}	collector-emitter cut-off current	V_{CE} = -120 V; V_{BE} = 0 V; T_{amb} = 25 °C		-	-	-100	nA
I_{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I_C = 0 A; T_{amb} = 25 °C		-	-	-100	nA
h_{FE}	DC current gain	V_{CE} = -10 V; I_C = -50 mA; T_{amb} = 25 °C		70	-	300	
		V_{CE} = -10 V; I_C = -100 mA; T_{amb} = 25 °C		60	-	300	
		V_{CE} = -10 V; I_C = -500 mA; pulsed; t_p ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C		50	-	300	
		V_{CE} = -10 V; I_C = -1 A; pulsed; t_p ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C		10	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = -100 mA; I_B = -10 mA; T_{amb} = 25 °C		-	-	-120	mV
		I_C = -100 mA; I_B = -20 mA; T_{amb} = 25 °C		-	-	-100	mV
		I_C = -500 mA; I_B = -100 mA; pulsed; t_p ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	-	-300	mV
V_{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -200 mA; pulsed; t_p ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	-	-1.2	V
t_d	delay time	V_{CC} = -6 V; I_C = -0.5 A; I_{Bon} = -0.1 mA; I_{Boff} = 0.1 mA; T_{amb} = 25 °C		-	10	-	ns
t_r	rise time			-	285	-	ns
t_{on}	turn-on time			-	295	-	ns
t_s	storage time			-	430	-	ns
t_f	fall time			-	300	-	ns
t_{off}	turn-off time			-	730	-	ns
f_T	transition frequency	V_{CE} = -10 V; I_C = -10 mA; f = 100 MHz; T_{amb} = 25 °C		-	55	-	MHz
C_c	collector capacitance	V_{CB} = -20 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	10	-	pF
C_e	emitter capacitance	V_{EB} = -0.5 V; I_C = 0 A; i_c = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	150	-	pF



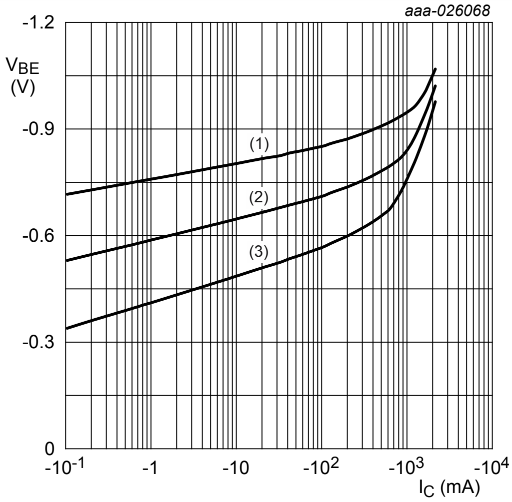
V_{CE} = -10 V
(1) T_{amb} = 100 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = −55 °C

Fig. 3. DC current gain as a function of collector current; typical values



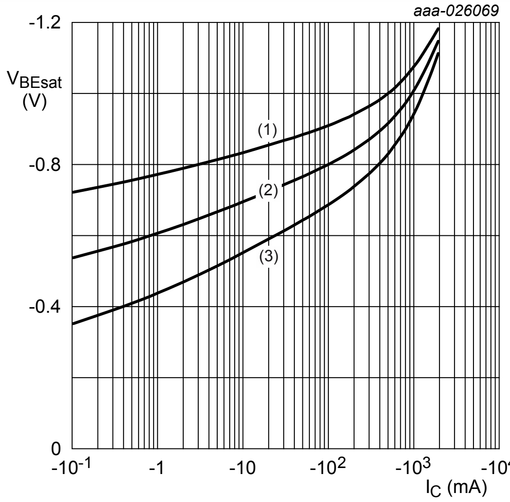
T_{amb} = 25 °C

Fig. 4. Collector current as a function of collector-emitter voltage; typical values



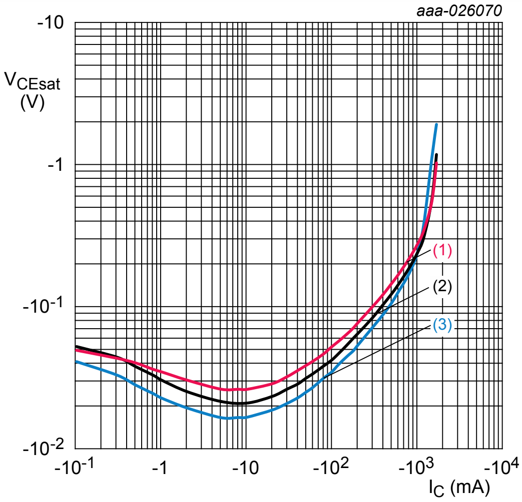
V_{CE} = -10 V
(1) T_{amb} = −55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 100 °C

Fig. 5. Base-emitter voltage as a function of collector current; typical values



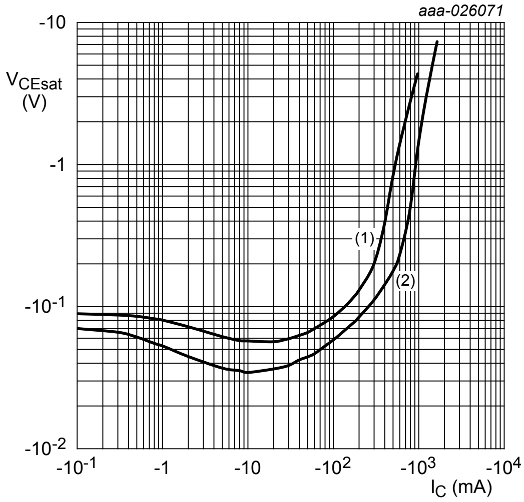
I_C/I_B = 5
(1) T_{amb} = −55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 100 °C

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



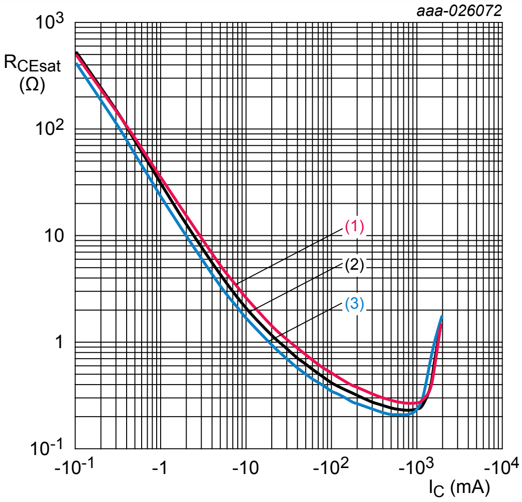
IC/IB = 5
(1) T_{amb} =100 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



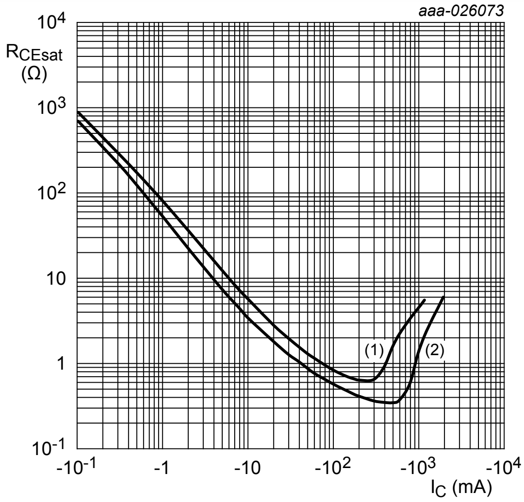
T_{amb} = 25 °C
(1) I_C/I_B = 20
(2) I_C/I_B = 10

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



I_C/I_B = 5
(1) T_{amb} = 100 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = −55 °C

Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values



T_{amb} = 25 °C
(1) I_C/I_B = 20
(2) I_C/I_B = 10

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

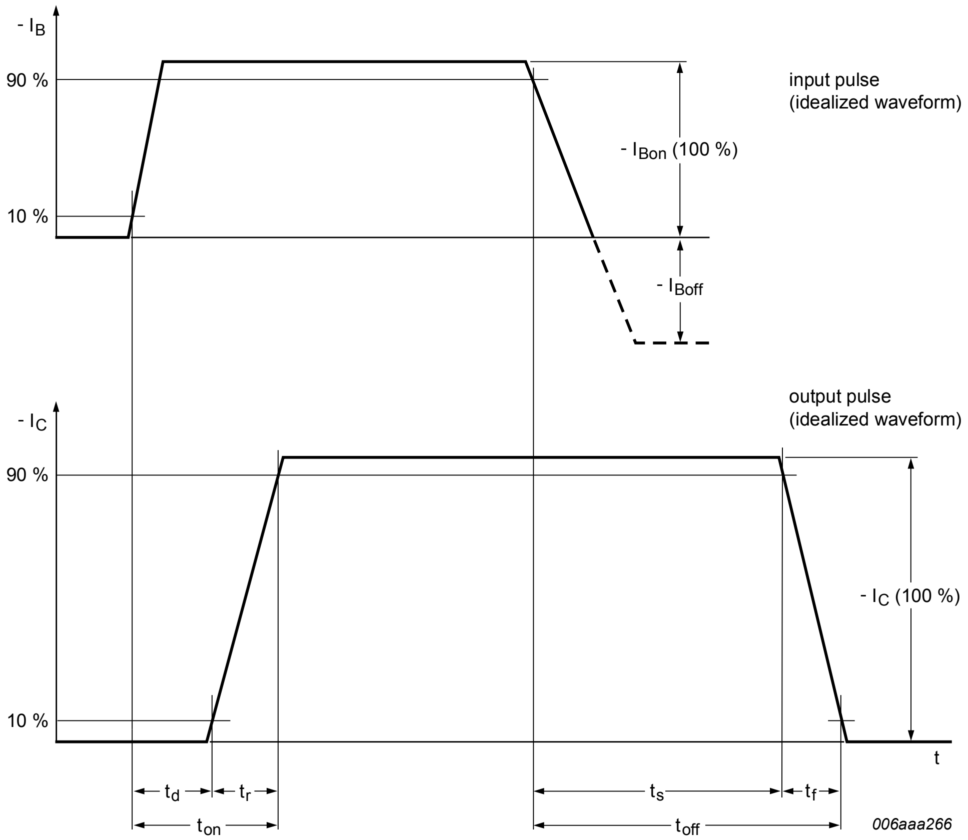


Fig. 11. BISS transistor switching time definition

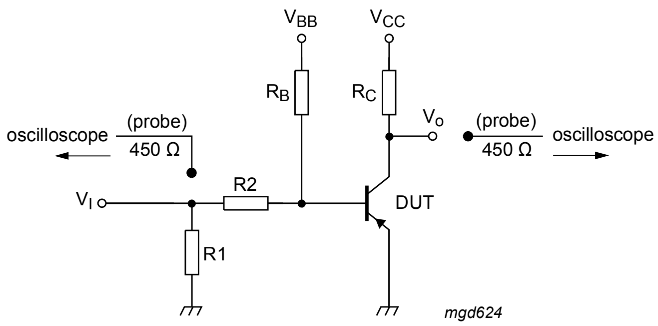


Fig. 12. Test circuit for switching times

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

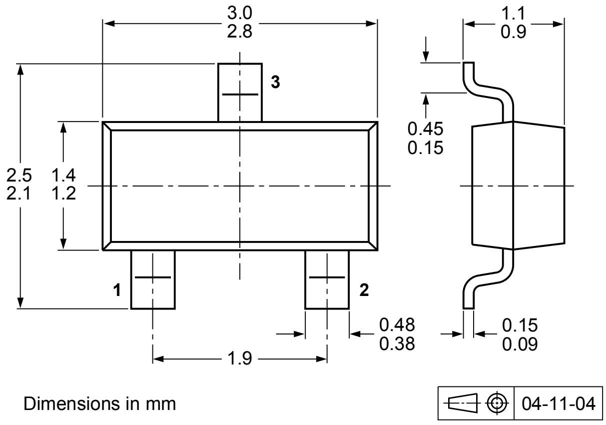


Fig. 13. Package outline TO-236AB (SOT23)

13. Soldering

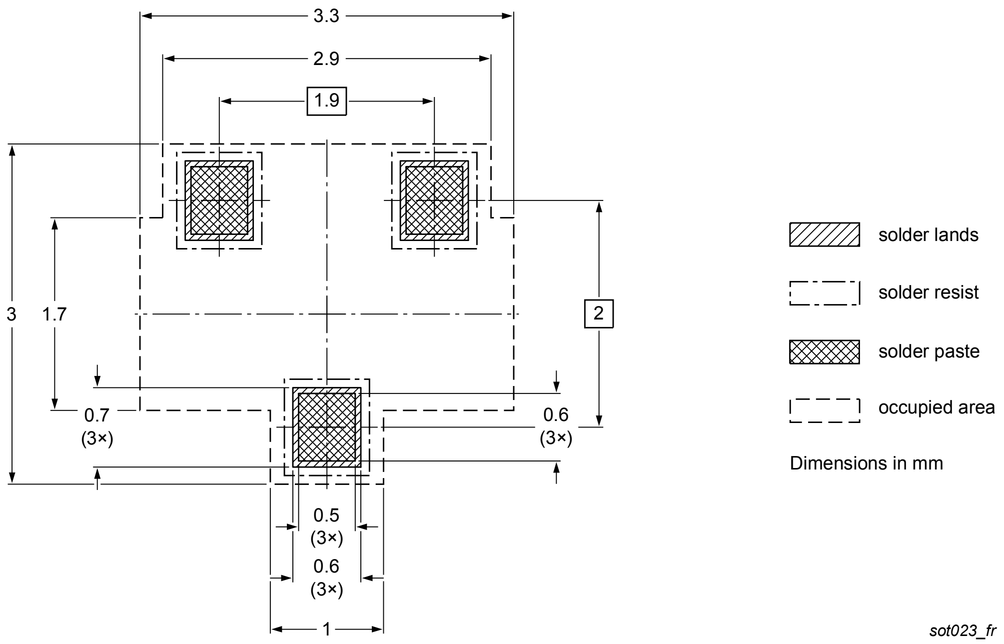


Fig. 14. Reflow soldering footprint for TO-236AB (SOT23)

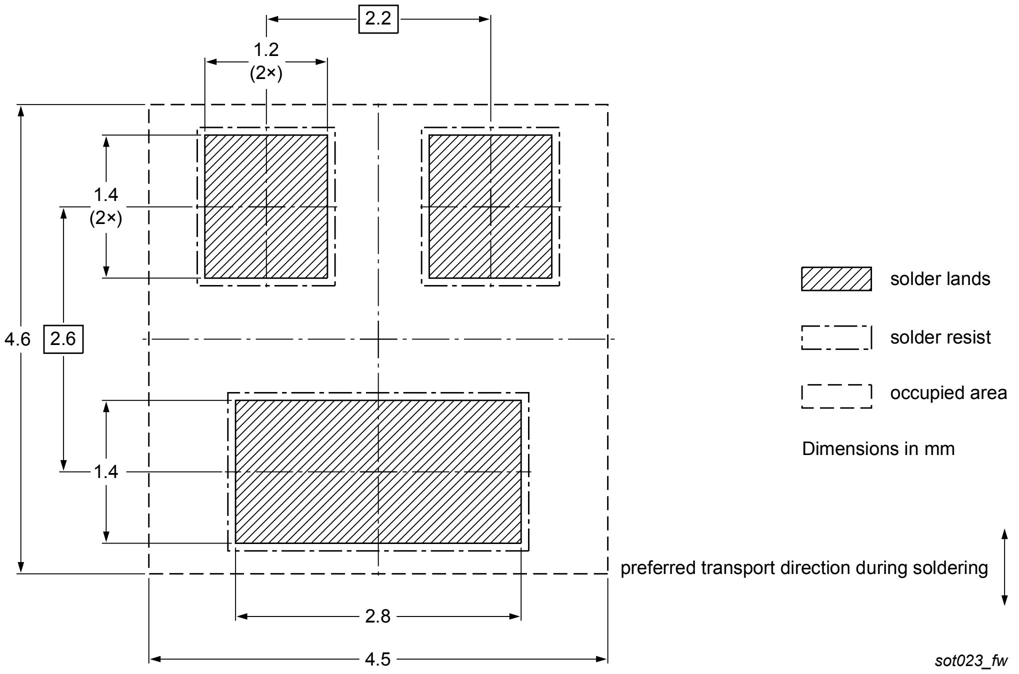


Fig. 15. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115TLH v.1	20170116	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
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